

Session U

Field Effect Transistors

Chairman:

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This session covers advances in microwave field effect transistors, including HEMTs for both low noise and power applications as well as a high linearity FET. In the first two papers, a pseudomorphic low noise HEMT (PHEMT) with 12 GHz noise figure of 0.6 dB and element reproducibility and an inverted PHEMT with improved characteristics are described. PHEMT with state-of-the-art power performance are described in the following two papers. Results include power-added efficiency of 65% at 10 GHz and output power approaching 0.7 w at 44 GHz. The potential of InP HEMTs for power applications is demonstrated in the fifth paper of the session. In the final paper, a FET with exceptional linearity-IP3 of 43 dBm at 10 GHz—is reported.

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1:30 p.m.–3:00 p.m., Wednesday, June 12, 1991
Ballroom A